

## AMENDMENTS TO THE CLAIMS

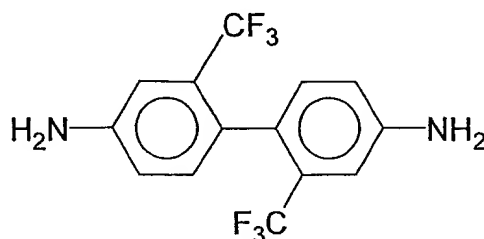
This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims:

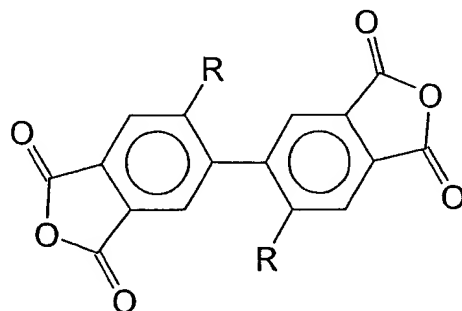
**Claim 1** (previously presented): An insulated integrated circuit comprising:

An integrated circuit; and

An insulating layer having a dielectric constant of less than about 2.5 is disposed on said integrated circuit, wherein said insulating layer is a polyimide film that is the polymerization product of polymerization product of an aromatic diamine having the general formula (I):

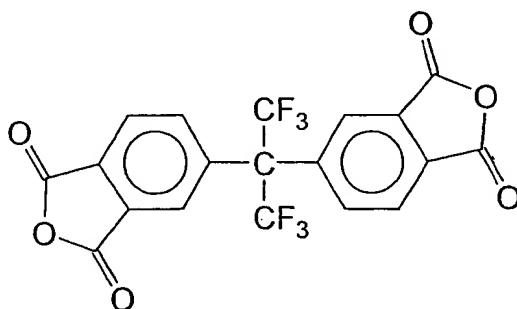


and an aromatic dianhydride having the formula (II):

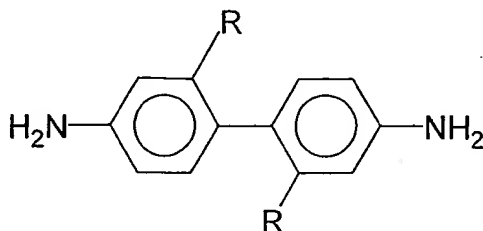


wherein R is an organic substituent selected from the group consisting of CF<sub>3</sub>, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5 bis[(m-trifluoromethyl) phenyl]; or

the polymerization product of an ormatic dianhydride having the general formula (III):



and an aromatic diamine having the formula (IV):



wherein R is a substituent selected from the group consisting of trifluoromethyl, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5'-bis[(m-trifluoromethyl) phenyl];

further wherein the dielectric constant of said insulating layer is less than about 2.5.

**Claim 2** (original): The insulated integrated circuit according to claim 1, wherein said integrated circuit is a microprocessor.

**Claim 3** (original): The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 1000 microns.

**Claim 4** (original): The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 500 microns.

**Claim 5** (original): The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 100 microns.

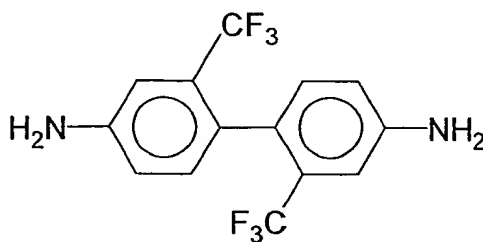
**Claims 6-8** (canceled)

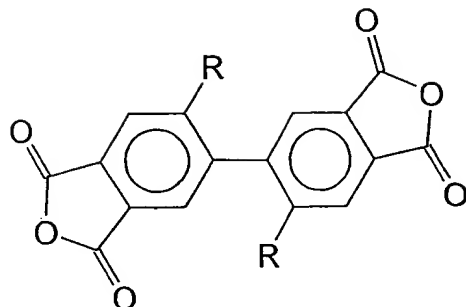
**Claim 9** (original): The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about  $23 \times 10^{-6}/^{\circ}\text{C}$ .

**Claim 10** (original): The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about  $42 \times 10^{-6}/^{\circ}\text{C}$ .

**Claim 11** (original): The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about  $50 \times 10^{-6}/^{\circ}\text{C}$ .

**Claim 12** (previously presented): An insulated electrically conductive component comprising:  
an electrically conductive component; and  
an insulating layer comprising the polymerization product of an aromatic diamine having the general formula (I):

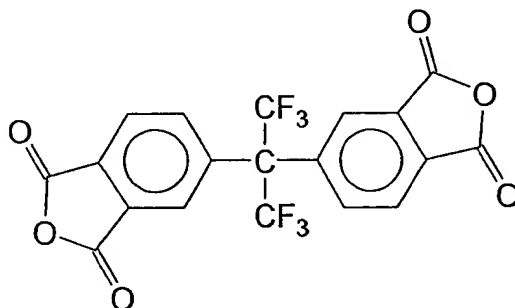




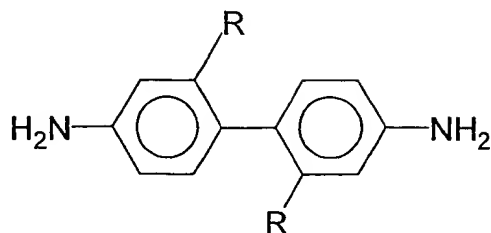
and an aromatic dianhydride having the formula (II):

wherein R is an organic substituent selected from the group consisting of  $\text{CF}_3$ , o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5-bis[(m-trifluoromethyl) phenyl]; or

the polymerization product of an aromatic dianhydride having the general formula (III):



and an aromatic diamine having the formula (IV):



wherein R is a substituent selected from the group consisting of trifluoromethyl, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5'-bis[(m-trifluoromethyl) phenyl], wherein

the coefficient of thermal expansion of the insulated electrically conductive component is greater than about  $23 \times 10^{-6}/^{\circ}\text{C}$ .

**Claim 13** (previously presented): The insulated electrically conductive component according to claim 12, wherein said electrically conductive component is selected from the group consisting of capacitors, diodes, connectors and transistors.

**Claim 14** (original): The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 1000 microns.

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**Claim 15 (original):** The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 500 microns.

**Claim 16 (original):** The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 100 microns.

**Claim 17 (original):** The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.8.

**Claim 18 (original):** The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.7.

**Claim 19 (original):** The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.5.

**Claim 20 (canceled)**

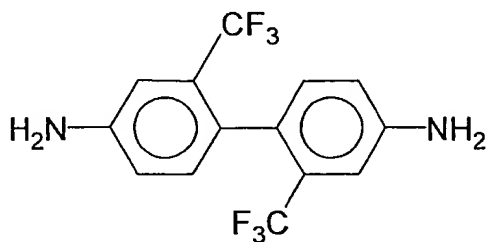
**Claim 21 (original):** The insulated electrically conductive component according to claim 12, wherein the coefficient of thermal expansion is greater than about  $42 \times 10^{-6}/^{\circ}\text{C}$ .

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**Claim 22** (original): The insulated electrically conductive component according to claim 1, wherein the coefficient of thermal expansion is greater than about  $50 \times 10^{-6}/^{\circ}\text{C}$ .

**Claim 23** (currently amended): A method of coating an integrated circuit comprising the steps of:

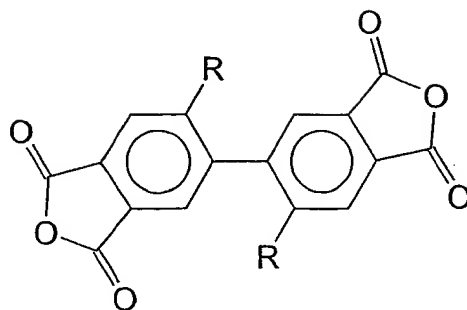
preparing a polyimide comprising the polymerization product of an aromatic diamine



having the general formula (I):

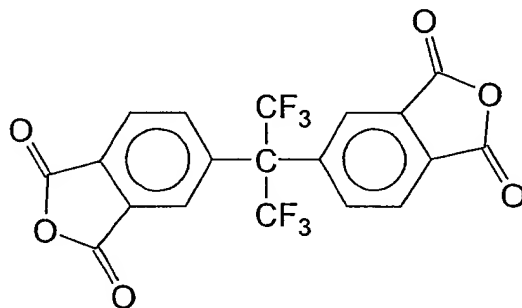


and an aromatic dianhydride having the formula (II):

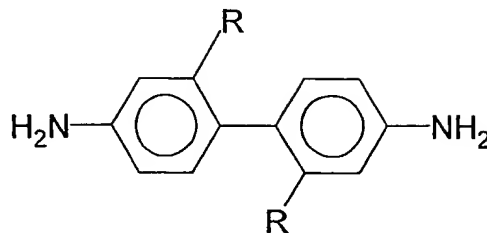


wherein R is an organic substituent selected from the group consisting of CF<sub>3</sub>, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5-bis[(m-trifluoromethyl) phenyl]; or

the polymerization product of an aromatic dianhydride having the general formula (III):



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and an aromatic diamine having the formula (IV):



wherein R is a substituent selected from the group consisting of trifluoromethyl, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5'-bis[(m-trifluoromethyl) phenyl];

applying the polyimide dispersed within an organic solvent to the surface of the integrated circuit forming a thin insulating layer or film on the surface of the circuit; and

heating the integrated circuit with the insulating polyimide layer or film disposed thereon to a temperature sufficient to evaporate the organic solvent and to cure the polyimide.

**Claim 24** (original): The method according to claim 23, wherein the step of applying includes one of spraying, dipping, spin-coating, brush-coating and flow-coating.

**Claim 25** (previously presented): The method according to claim 23, wherein the organic solvent is selected from the group consisting of acetone, cyclopentanone, tetrahydrofuran (THF), N,N'-dimethylacetamide (DMAc), N,N'-dimethylformamide (DMF), N-methylpyrrolidone (NMP) p-chlorophenol and m-cresol.